

6367254 MOTOROLA SC (XSTRS/R F)

89D 79021 DT-33-15

**MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA**

**MRF458
MRF458A**

The RF Line

NPN SILICON RF POWER TRANSISTOR

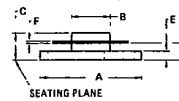
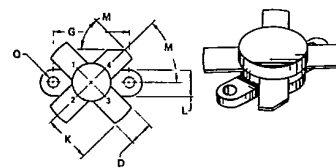
... designed for power amplifier applications in industrial, commercial and amateur radio equipment to 30 MHz.

- Specified 12.5 Volt, 30 MHz Characteristics -
 - Output Power = 80 Watts
 - Minimum Gain = 12 dB
 - Efficiency = 50%
- Capable of Withstanding 30:1 Load VSWR @ Rated P_{out} and V_{CC}

80 W-30 MHz

**RF POWER
TRANSISTOR**

NPN SILICON



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	24.64	24.89	0.970	0.980
B	11.81	12.95	0.465	0.510
C	5.82	6.38	0.233	0.255
D	5.46	5.97	0.216	0.235
E	2.13	2.79	0.084	0.110
F	0.09	0.18	0.003	0.007
G	18.28	18.64	0.720	0.730
H	11.05	-	0.435	-
I	6.22	6.49	0.246	0.255
J	45° NOM	45° NOM	-	-
K	3.65	4.52	0.144	0.178
L	2.92	3.30	0.115	0.130

STYLE 1
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

CASE 211-11

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	18	Vdc
Collector-Base Voltage	V _{CBO}	36	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector Current - Continuous	I _C	10	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	175 1.0	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

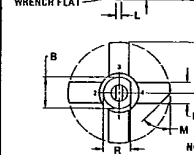
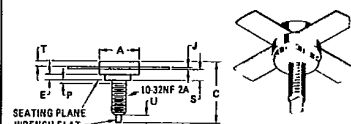
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.0	°C/W

MATCHING PROCEDURE

In the push-pull circuit configuration, it is preferred that the transistors are used as matched pairs to obtain optimum performance.

The matching procedure used by Motorola consists of measuring h_{FE} at the data sheet conditions and color coding the device to predetermined h_{FE} ranges within the normal h_{FE} limits. A color dot is added to the marking on top of the cap. Any two devices with the same color dot can be paired together to form a matched set of units.



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	12.45	12.95	0.480	0.510
B	10.54	10.80	0.415	0.425
C	19.60	22.73	0.775	0.895
D	5.46	5.97	0.215	0.235
E	1.83	-	0.072	-
F	0.09	0.18	0.003	0.007
G	12.45	-	0.490	-
H	1.65	1.80	0.065	0.075
I	45° NOM	45° NOM	-	-
J	-	1.27	-	0.050
K	9.73	10.06	0.383	0.395
L	3.84	4.60	0.151	0.177
M	2.11	2.54	0.083	0.100
N	2.49	3.35	0.098	0.132

STYLE 1:
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

CASE 145A-10

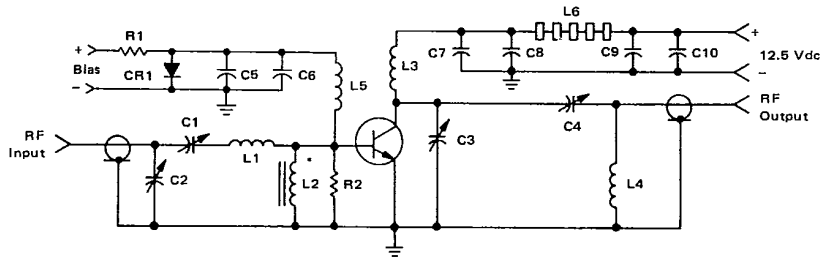
MRF458, MRF458A

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I _C = 100 mA, I _B = 0)	V(BR)CEO	18	—	—	Vdc
Collector-Base Breakdown Voltage (I _C = 50 mA, I _E = 0)	V(BR)CBO	36	—	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 mA, I _C = 0)	V(BR)EBO	4.0	—	—	Vdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 5.0 Vdc)	h _{FE}	10	—	150	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 15 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	—	—	300	pF
FUNCTIONAL TESTS (Figure 1)					
Common-Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{out} = 80 W, f = 30 MHz)	G _{PE}	12	—	—	dB
Collector Efficiency (V _{CC} = 12.5 Vdc, P _{out} = 80 W, f = 30 MHz)	η	50	—	—	%
Intermodulation Distortion (V _{CC} = 12.5 Vdc, P _{out} = 70 W PEP, f = 30, 30.001 MHz)	IMD ₃ IMD ₅	—	-32 -35	—	dB

3

FIGURE 1 — 30 MHz TEST CIRCUIT SCHEMATIC



- C1, C2, C4 — ARCO 469
- C3 — ARCO 466
- C5 — ERIE 0.1 μF, 100 V
- C6 — 500 μF, 15 V Electrolytic
- C7 — 1000 pF, UNELCO
- C8, C9 — 0.1 μF Disk Ceramic
- C10 — 100 μF, 15 V Electrolytic
- CR1 — 1N4997
- R1 — 10 Ω, 25 Watt Wirewound
- R2 — 10 Ohm, 1 Watt, Carbon

- L1 — 3 Turns #18 AWG, 5/16" I.D., 5/16" Long
- L2, L5 — VK200 — 20/4B, FERROXCUBE
- L3 — 12 Turns, #18 AWG Enamelled Wire, 1/4" I.D., Close Wound
- L4 — 3 Turns 1/8" O.D. Copper Tubing, 3/8" I.D., 3/4" Long
- L6 — 7 FERRITE Beads, FERROXCUBE #66-690-65/3B

*NOTE: For Class C operation bias network (R1, R2, CR1, C5, C6, L5) is not used.
For Class AB operation L2 is not used.

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89D 79023 DT-33-15

TYPICAL PERFORMANCE CURVES

FIGURE 2 - POWER GAIN versus FREQUENCY

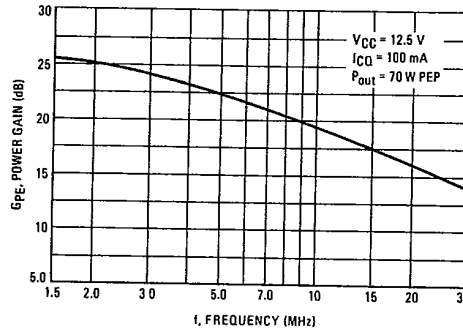


FIGURE 3 - OUTPUT RESISTANCE versus FREQUENCY

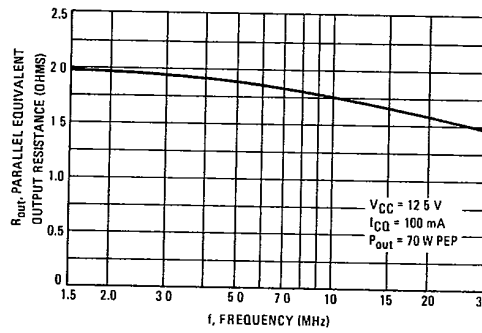
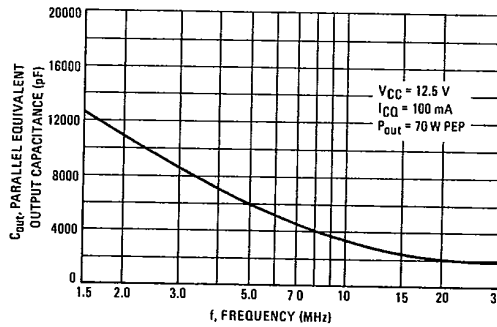


FIGURE 4 - OUTPUT CAPACITANCE versus FREQUENCY

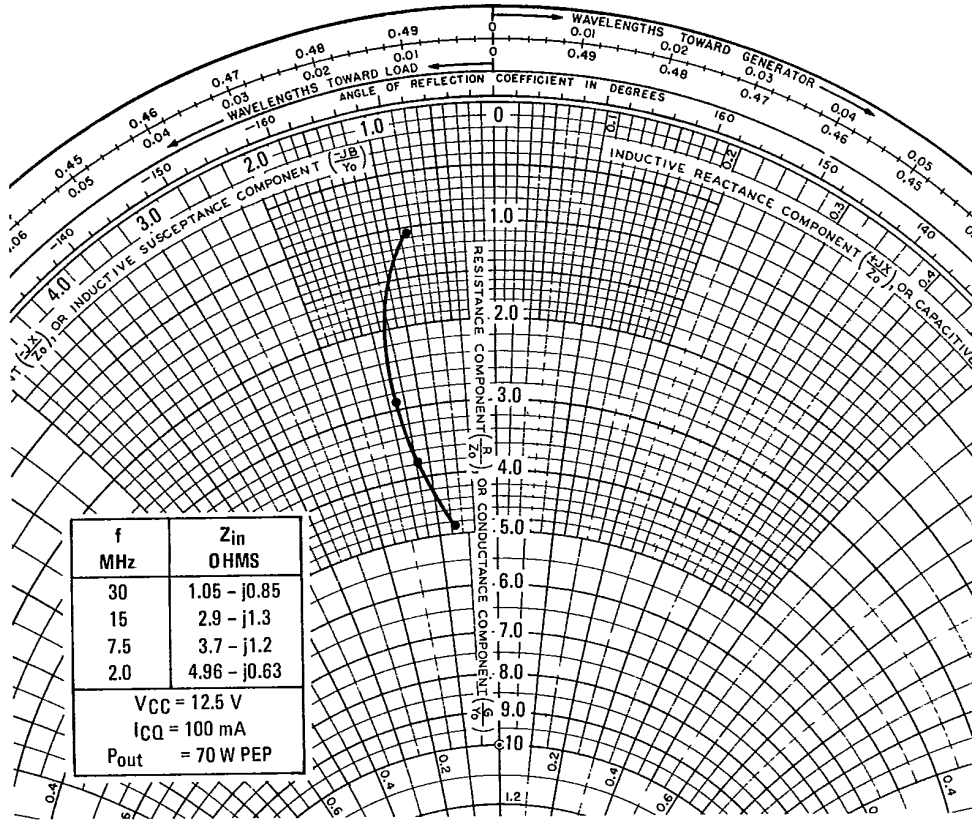


3

6367254 MOTOROLA SC (XSTRS/R F)
MRF458, MRF458A

89D 79024 DT-33-15

FIGURE 5 - SERIES EQUIVALENT INPUT-OUTPUT IMPEDANCE



3